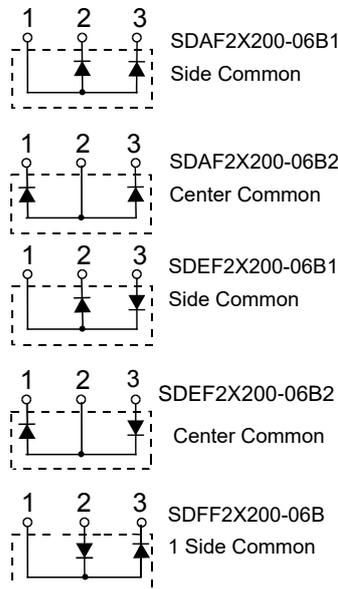
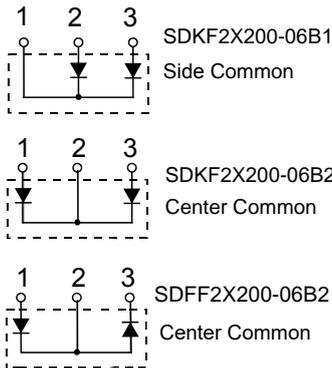
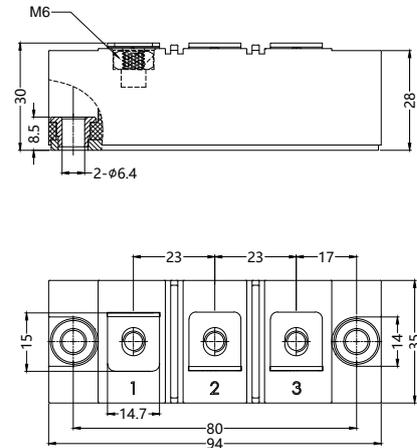


# SDKF/SDAF/SDEF/SDFF2x200-06B1(B2)

## Soft Recovery Behaviour Ultra Fast Recovery Epitaxial Diode Modules



Dimensions in mm (1mm=0.0394")



	VRSM	VRRM
	V	V
SDKF2x200-06B1	600	600
SDKF2x200-06B2	600	600

	VRSM	VRRM
	V	V
SDEF2x200-06B1	600	600
SDEF2x200-06B2	600	600

	VRSM	VRRM
	V	V
SDAF2x200-06B1	600	600
SDAF2x200-06B2	600	600

	VRSM	VRRM
	V	V
SDFF2x200-06B1	600	600
SDFF2x200-06B2	600	600

### FEATURES

- \* International standard package
- \* Copper Base Plate
- \* Planar passivated chips
- \* Short recovery time
- \* Low switching losses
- \* Soft recovery behaviour
- \* Isolation voltage 4800 V~
- \* RoHS compliant

### APPLICATIONS

- \* Antiparallel diode for high frequency switching devices
- \* Free wheeling diode in converters and motor control circuits
- \* Inductive heating and melting
- \* Uninterruptible power supplies (UPS)
- \* Ultrasonic cleaners and welders

### ADVANTAGES

- \* High reliability circuit operation
- \* Low voltage peaks for reduced protection circuits
- \* Low noise switching
- \* Low losses



# SDKF/SDAF/SDEF/SDFF2x200-06B1(B2)

## Soft Recovery Behaviour Ultra Fast Recovery Epitaxial Diode Modules

Symbol	Test Conditions	Maximum Ratings	Unit
<b>IFRMS</b> <b>IFAVM</b> <b>IFRM</b>	$T_C=75^{\circ}\text{C}$ $T_C=75^{\circ}\text{C}$ ; rectangular, $d=0.5$ $t_p < 10\mu\text{s}$ ; rep. rating, pulse width limited by $T_{VJM}$	284 2 x 200 1600	A
<b>IFSM</b>	$T_{VJ}=45^{\circ}\text{C}$ $t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	3040 3300	A
	$T_{VJ}=150^{\circ}\text{C}$ $t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	2700 2960	
<b>I<sup>2</sup>t</b>	$T_{VJ}=45^{\circ}\text{C}$ $t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	45500 45000	A <sup>2</sup> s
	$T_{VJ}=150^{\circ}\text{C}$ $t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	38800 39200	
<b>T<sub>VJ</sub></b> <b>T<sub>stg</sub></b> <b>T<sub>Hmax</sub></b>		-40...+150 -40...+125 110	°C
<b>P<sub>tot</sub></b>	$T_{\text{case}}=25^{\circ}\text{C}$	690	W
<b>V<sub>ISOL</sub></b>	50/60Hz, RMS $t=1\text{min}$ $I_{\text{ISOL}} \leq 1\text{mA}$ $t=1\text{s}$	4000 4800	V~
<b>M<sub>d</sub></b>	Mounting torque (M6) Terminal connection torque (M6)	2.50-4/22-35 2.50-4/22-35	Nm/lb.in.
<b>ds</b> <b>da</b> <b>a</b>	Creeping distance on surface Strike distance through air Maximum allowable acceleration	12.7 9.6 50	mm mm m/s <sup>2</sup>
<b>Weight</b>		170	g

Symbol	Test Conditions	Characteristic Values		Unit
		typ.	max.	
<b>I<sub>R</sub></b>	$T_{VJ}=25^{\circ}\text{C}$ ; $V_R=V_{RRM}$		0.5	mA
	$T_{VJ}=25^{\circ}\text{C}$ ; $V_R=0.8 \cdot V_{RRM}$		0.2	
	$T_{VJ}=125^{\circ}\text{C}$ ; $V_R=0.8 \cdot V_{RRM}$		1	
<b>V<sub>F</sub></b>	$I_F=200\text{A}$ ; $T_{VJ}=125^{\circ}\text{C}$ $T_{VJ}=25^{\circ}\text{C}$	1.35	1.40 2.00	V
	$I_F=400\text{A}$ ; $T_{VJ}=125^{\circ}\text{C}$ $T_{VJ}=25^{\circ}\text{C}$		1.80 2.30	
<b>V<sub>Fo</sub></b>	For power-loss calculations only		0.99	V
<b>r<sub>F</sub></b>	$T_{VJ}=125^{\circ}\text{C}$		2.90	mΩ
<b>R<sub>thJH</sub></b> <b>R<sub>thJC</sub></b>	DC current		0.290	K/W
	DC current		0.140	
<b>t<sub>rr</sub></b>	$I_F=1\text{A}$ ; $T_{VJ}=25^{\circ}\text{C}$ $di/dt=200\text{A}/\mu\text{s}$	40	50	ns
	$I_F=200\text{A}$ ; $T_{VJ}=100^{\circ}\text{C}$ $di/dt=200\text{A}/\mu\text{s}$	100	130	
<b>I<sub>RM</sub></b>	$V_R=300\text{V}$ ; $T_{VJ}=25^{\circ}\text{C}$		75	A
	$-di/dt=200\text{A}/\mu\text{s}$ ; $T_{VJ}=100^{\circ}\text{C}$		102	A

**Sirectifier**<sup>®</sup>

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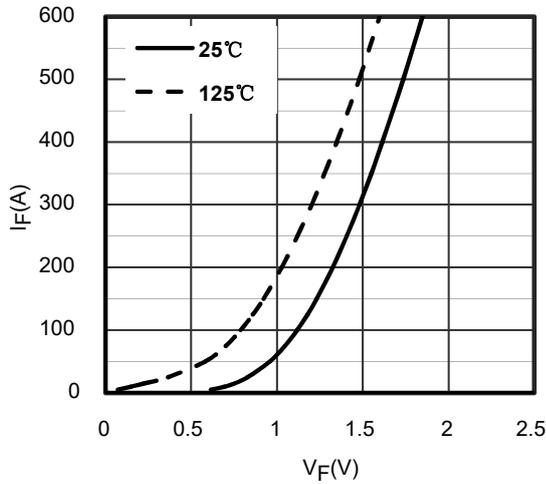


Fig 1. Forward Voltage Drop vs Forward Current

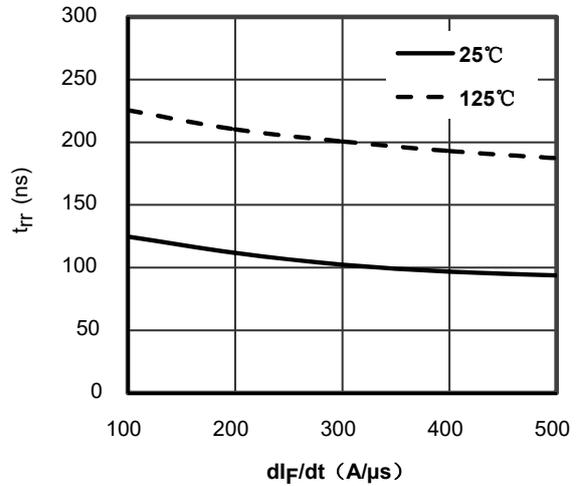


Fig 2. Reverse Recovery Time vs dIF/dt

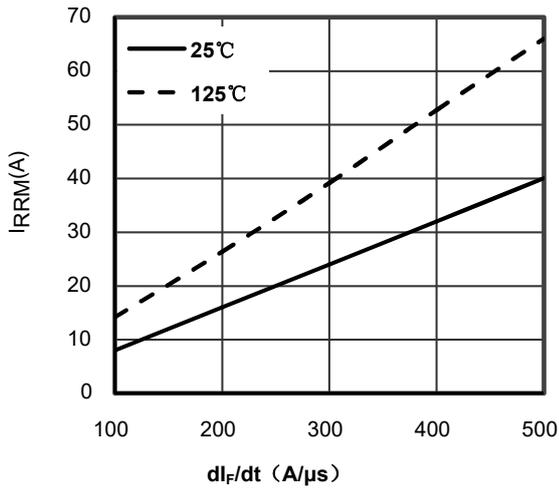


Fig 3. Reverse Recovery Current vs dIF/dt

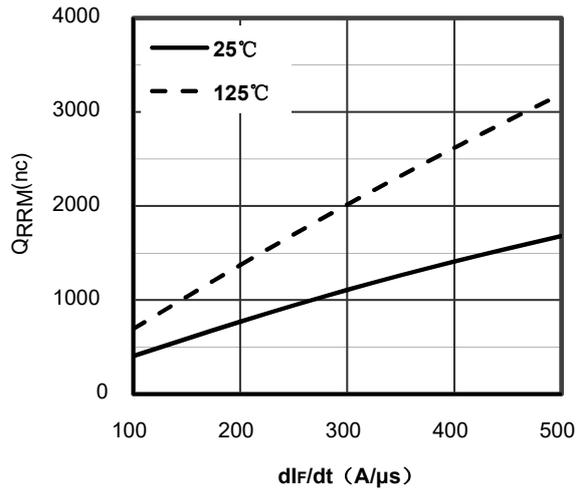


Fig 4. Reverse Recovery Charge vs dIF/dt

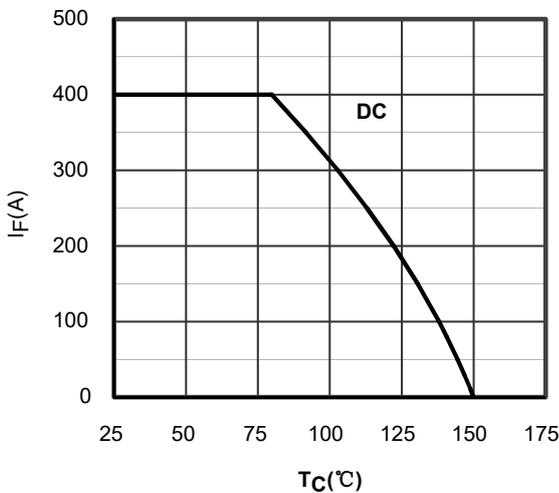


Fig 5. Forward current vs Case temperature

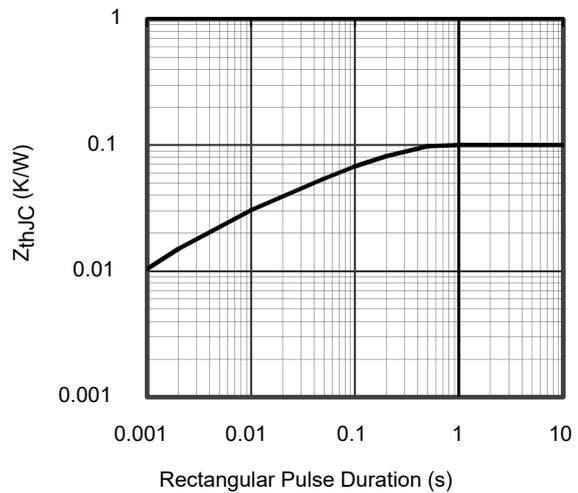


Fig 6. Transient Thermal Impedance